

WHAT IS CLAIMED IS:

1. A high frequency semiconductor integrated circuit comprising:
a main circuit having an active element and a first pad therein;
a circuit block constituted of a passive element;
a second pad connected to said circuit block; and
5 a wire to connect said first pad to said second pad.
2. The high frequency semiconductor integrated circuit according to
claim 1, wherein said main circuit includes said active element and said
first pad between an input terminal and an output terminal.
3. The high frequency semiconductor integrated circuit according to
claim 2, wherein said circuit block includes a passive element whose
impedance decreases with increase in frequency of an input signal inputted
at said input terminal.
4. The high frequency semiconductor integrated circuit according to
claim 2, wherein said circuit block includes an interconnect connected to
said second pad and the sum of a length of said wire and a length of said
interconnect is equal to one-fourth of a wavelength of a high frequency
5 signal inputted at said input terminal.
5. A high frequency semiconductor integrated circuit comprising:
a main circuit having an active element and a main pad therein;
plural circuit blocks each constituted of a passive element;
plural connection pads provided correspondingly to said respective
5 plural circuit blocks; and
a wire for connecting said main pad to one of said plural connection
pads.
6. The high frequency semiconductor integrated circuit according to
claim 5, wherein said main circuit includes: said active element; and said

main pad between an input terminal and an output terminal.

7. The high frequency semiconductor integrated circuit according to claim 6, wherein said plural circuit blocks include:

a first circuit block for adjusting an impedance of said main circuit to be a first impedance;

5 a second circuit block for adjusting said impedance of said main circuit to be a second impedance; and

a third circuit block for adjusting said impedance of said main circuit to be a third impedance.

8. The high frequency semiconductor integrated circuit according to claim 7, wherein said first circuit block is constituted of a first capacitor having a first capacity, and connected to a ground node at one end thereof and a first connection pad at the other end thereof,

5 said second circuit block is constituted of a second capacitor having a second capacity, and connected to the ground node at one end thereof and a second connection pad at the other end thereof and

10 said third circuit block is constituted of a third capacitor having a third capacity, and connected to the ground node at one end thereof and a third connection pad at the other end thereof.

9. A high frequency semiconductor integrated circuit comprising:

a first high frequency semiconductor integrated circuit;

a second high frequency semiconductor integrated circuit; and

5 a main wire for connecting said first high frequency semiconductor integrated circuit to said second high frequency semiconductor integrated circuit.

10. The high frequency semiconductor integrated circuit according to claim 9, wherein said first high frequency semiconductor integrated circuit comprises a main circuit having an active element and a circuit block having a passive element; and

5 said second high frequency semiconductor integrated circuit includes only a main circuit having an active element.

11. The high frequency semiconductor integrated circuit according to claim 10, wherein said second high frequency semiconductor integrated circuit includes:

5 a first main circuit having a first active element and a first pad, and said first high frequency semiconductor integrated circuit includes:
a circuit block having a passive element;
a second pad connected to said circuit block;
a second main circuit having a third pad for connecting said first and
10 second pads to each other, and a second active element; and
a wire for connecting said second pad to said third pad,
wherein said main wire connects said first pad to said third pad.

12. The high frequency semiconductor integrated circuit according to claim 11, wherein said first main circuit further includes:

5 an interconnect connected to said first pad at one end thereof and said first active element at the other end thereof; and
an output terminal connected to said first active element, and
said second main circuit further includes:
an interconnect connected to said third pad at one end thereof and
said second active element at the other end thereof; and
an input terminal connected to said second active element.

13. The high frequency semiconductor integrated circuit according to claim 12, wherein said circuit block includes: a passive element for matching an impedance of said first main circuit to an impedance of said second main circuit.

14. The high frequency semiconductor integrated circuit according to claim 9, wherein said first high frequency semiconductor integrated circuit includes only a main circuit having an active element and

said second high frequency semiconductor integrated circuit includes
5 only a circuit block having a passive element.

15. The high frequency semiconductor integrated circuit according
to claim 14, wherein said first high frequency semiconductor integrated
circuit includes a main circuit having an active element and a main pad,
and

5 said second high frequency semiconductor integrated circuit includes
plural circuit blocks each having a passive element, and

plural connection pads provided correspondingly to said respective
plural circuit blocks, wherein said main wire connects said main pad to one
of said plural connection pads.